

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

MCH6122 — PNP Epitaxial Planar Silicon Transistor DC / DC Converter Amplifier

Applications

· Relay drivers, lamp drivers, motor drivers, charger circuit

Features

- · Adoption of MBIT process
- · Low collector-to-emitter saturation voltage
- · Large current capacity · High speed switching

- \cdot Ultrasmall-sized package permitting applied sets to be made small and slim (0.85mm)
- · High allowable power dissipation
- · Halogem free compliance

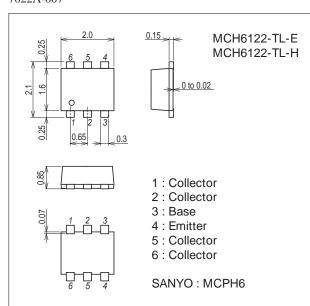
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		-30	V
Collector-to-Emitter Voltage	VCEO		-30	V
Emitter-to-Base Voltage	VEBO		-5	V
Collector Current	IC		-3	Α
Collector Current (Pulse)	ICP		-5	Α
Base Current	IB		-600	mA
Collector Dissipation	PC	When mounted on ceramic substrate (600mm ² ×0.8mm)	1	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit: mm (typ) 7022A-007



Product & Package Information

 Package : MCPH6

• JEITA, JEDEC : SC-88, SC-70-6, SOT-363

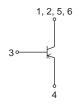
• Minimum Packing Quantity : 3,000 pcs./reel

Packing Type: TL

Marking



Electrical Connection



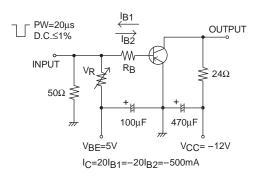
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Electrical Characteristics at Ta=25°C

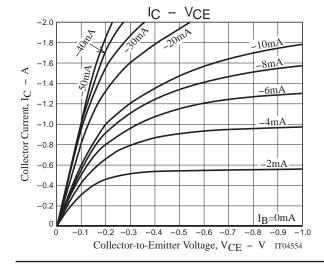
Parameter	Cumbal	Conditions	Ratings			Linit	
Parameter	Symbol	Conditions	min	typ	max	Unit	
Collector Cutoff Current	ICBO	VCB= -30V, IE=0A			-0.1	μΑ	
Emitter Cutoff Current	IEBO	V _{EB} = -4V, I _C =0A			-0.1	μΑ	
Collector Cutoff Current	IECO	V _{EC} = -4.5V, I _B =0A			-1	μΑ	
DC Current Gain	hFE	V _{CE} = -2V, I _C = -500mA	200		560		
Gain-Bandwidth Product	fŢ	VCE= -10V, IC= -500mA		400		MHz	
Output Capacitance	Cob	V _{CB} = -10V, f=1MHz		25		pF	
Collector to Emitter Seturation Valtage	VCE(sat)1	I _C = -1.5A, I _B = -30mA		-180	-270	mV	
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)2	I _C = -1.5A, I _B = -75mA		-120	-180	mV	
Base-to-Emitter Saturation Voltage	VBE(sat)	IC= -1.5A, IB= -30mA		-0.83	-1.2	V	
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC= -10μA, IE=0A	-30			V	
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC= -1mA, RBE=∞	-30			V	
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E = -10μA, I _C =0A	-5			V	
Turn-On Time	ton			50		ns	
Storage Time	tstg	See specified Test Circuit.		270		ns	
Fall Time	tf			27		ns	

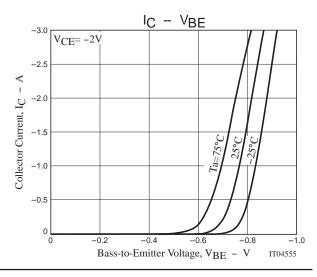
Switching Time Test Circuit

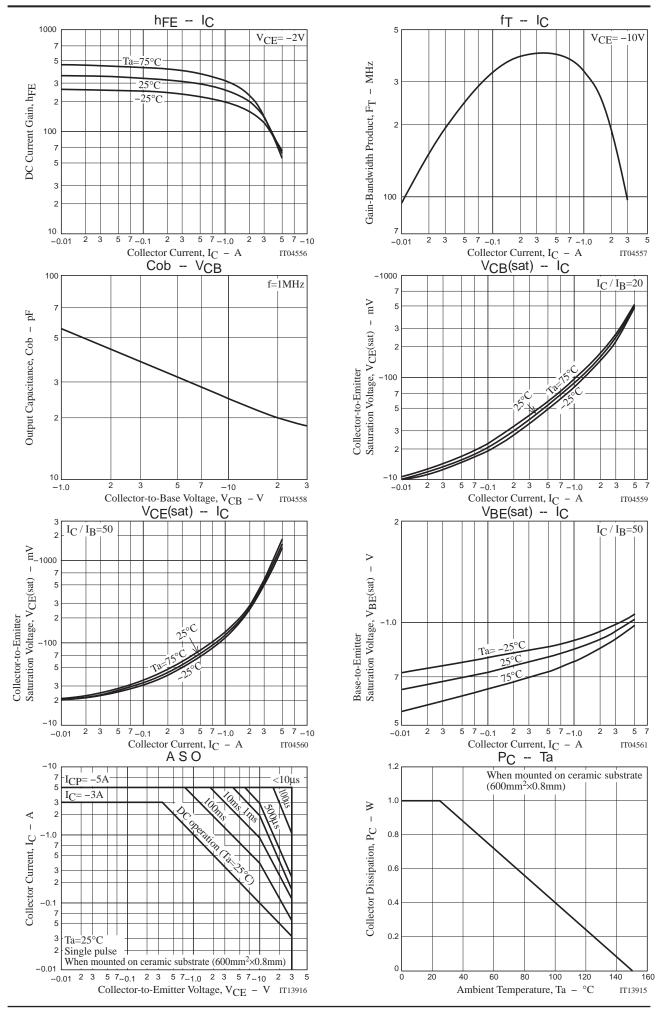


Ordering Information

Device	Package	Shipping	memo	
MCH6122-TL-E MCPH6		3,000pcs./reel Pb Free		
MCH6122-TL-H	МСРН6	3,000pcs./reel	Pb Free and Halogen Free	





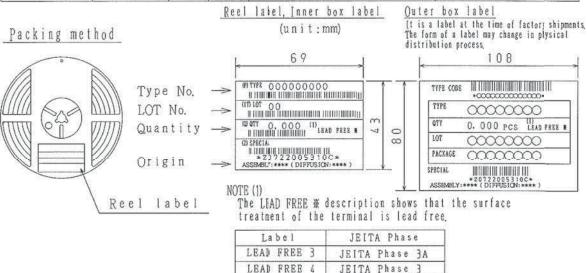


Embossed Taping Specification

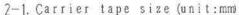
MCH6122-TL-E, MCH6122-TL-H

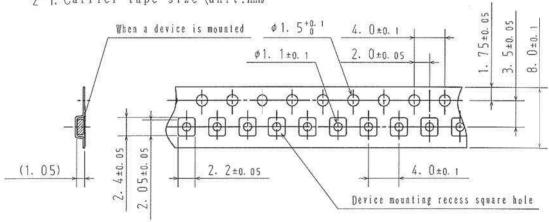
1. Packing Format

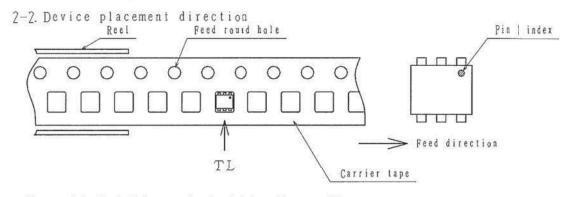
850	Carrier Tape	Maximum Number of devices contained (cs)			Packing format		
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)	
МСРН6	MCP4	3, 000	15, 000	90, 000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210	



2. Taping configuration





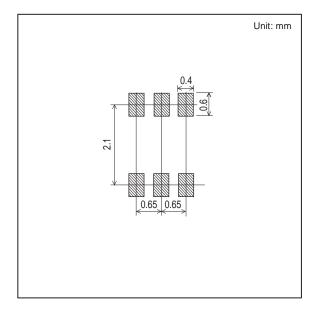


Those with pin 1 index on the feed hole side ·····TL

Outline Drawing

MCH6122-TL-E, MCH6122-TL-H

Land Pattern Example



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